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**CONTINUED PROSECUTION APPLICATION (CPA)
UNDER 37 C.F.R. § 1.53(d)
REQUEST TRANSMITTAL**

#11/CPA
8/19/99
V. Vannall

Address to: Assistant Commissioner for Patents Box CPA Washington, D.C. 20231	Attorney Docket No.:	303.229US2
	First Named Inventor:	Leonard Forbes
	Express Mail No.:	EL334875593US
	Total Pages (if by fax):	0

This is a request for filing a continuation application under 37 CFR § 1.53(d) of prior application Serial No. 09/132,157, filed on August 11, 1998, entitled SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH.

The above-identified prior application in which no abandonment of, or termination of, proceedings has occurred, is hereby expressly abandoned as of the filing date of this request for a CPA. Please use all the contents of the prior application file wrapper, including the drawings, as the basic papers for the new application. (37 CFR 1.53(b) must be used for continuation-in-part applications or for applications where the prior application is not to be abandoned.)

1. ☐ Enter the amendment previously filed on ☐ under 37 CFR 1.116, but unentered, in the prior application.
2. ☒ A Preliminary Amendment (7 pages) is enclosed. ✓
3. ☐ This application is filed by fewer than all the inventors named in the prior application, 37 CFR 1.53(d)(4).
 - a. ☐ **DELETE** the following inventor(s) named in the prior nonprovisional application:

 - b. ☐ The inventor(s) to be deleted are set forth on a separate sheet attached hereto.
4. ☐ A new power of attorney is enclosed.
5. ☐ Information Disclosure Statement is enclosed.
 - a. ☐ Form(s) 1449
 - b. ☐ Copies of IDS Citations

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09/10/1999 SLURRG1 00000024 09132157

01 FDC131 760.00 CP
02 FDC102 156.00 OP

CONTINUED PROSECUTION APPLICATION (CPA) REQUEST TRANSMITTAL

Page 2 of 2

Inventors: Leonard Forbes

Prior Application No.: 09/132,157

The filing fee is calculated below on the basis of the claims existing in the prior application as amended at 1 and 2 on the previous page:

	No. Filed	No. Extra	Rate	Fee
TOTAL CLAIMS	13 - 20 =	0	x 18 =	\$0.00
INDEPENDENT CLAIMS	5 - 3 =	2	x 78 =	\$156.00
[] MULTIPLE DEPENDENT CLAIMS PRESENTED				\$0.00
BASIC FEE				\$760.00
TOTAL				\$916.00

6. ☐ Small Entity Status:

- a. ☐ A small entity statement is enclosed.
- b. ☐ A small entity statement was filed in the prior nonprovisional application and such status is still proper and desired.
- c. ☐ Is no longer claimed.

7. ☒ A check in the amount of \$916.00 is attached to pay the filing fee.8. ☒ The Commissioner is hereby authorized to credit overpayments or charge any fees set forth in 37 CFR 1.16 through 1.18 to Deposit Account No. 19-0743.9. ☐ A petition for extension of time in the prior application is enclosed along with a check in the amount of \$0.00 to pay the extension fee.10. ☐ Other : _____

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

By: Thomas W. Leffert
Atty: Thomas W. Leffert
Reg. No. 40,697

Customer Number **21186**"Express Mail" mailing label number EL334875593USDate of Deposit August 11, 1999

I hereby certify that this paper or fee is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 C.F.R. 1.10 on the date indicated above and is addressed to Box CPA, Assistant Commissioner for Patents, Washington, D. C. 20231

Chris Hammond
Printed Name

Chris Hammond
Signature



S/N 09/132,157

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes

Examiner: Mark Prenty

Serial No.: 09/132,157

Group Art Unit: 2822

Filed: August 11, 1998

Docket: 303.229US2

Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION
IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

12/D
8/19/99
V. Vannelli

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the final Office Action mailed May 28, 1999. Please amend the above-identified application as follows.

IN THE CLAIMS

Please cancel claim ~~33-37~~. Please amend claims 11, 24, 25, 28 and 30 as follows:

11. (Twice Amended) A semiconductor transistor, comprising:
- a silicon substrate;
 - a gate oxide, coupled to the substrate;
 - a gate, coupled to the gate oxide;
 - source/drain regions formed in the substrate on opposite sides of the gate; and
 - a Si_{1-x}Ge_x channel region, having a germanium molar fraction of x, and formed in the substrate, underneath and [adjacent]adjoining the gate oxide and between the source/drain regions;
- wherein the Si_{1-x}Ge_x channel region has a channel length less than 7μm.

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